

Title (en)  
THERMOCOMPRESSSION BONDING WITH RAISED FEATURE

Title (de)  
THERMOKOMPRESSSIONSSCHWEISSEN MIT ERHÖHTEM MERKMAL

Title (fr)  
LIAISON PAR THERMOCOMPRESSSION AVEC CARACTÉRISTIQUES SUR ÉLEVÉES

Publication  
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Application  
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Abstract (en)  
[origin: WO2017213652A1] A method for bonding two substrates is described, comprising providing a first and a second silicon substrate, providing a raised feature on at least one of the first and the second silicon substrate, forming a layer of gold on the first and the second silicon substrates, and pressing the first substrate against the second substrate, to form a thermocompression bond around the raised feature. The high initial pressure caused by the raised feature on the opposing surface provides for a hermetic bond without fracture of the raised feature, while the complete embedding of the raised feature into the opposing surface allows for the two bonding planes to come into contact. This large contact area provides for high strength.

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Citation (search report)

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